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FORM PTO-1449 (Modified)					ATTY. DOCKET NO.			SERIAL NO.:		
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION					YOR919990123US2			09/936,320		
DISCLOSURE STATEMENT					APPLICANT: Jack O. Chu					
(Use several sheets if necessary)			THE PROPERTY		FILING DATE: September 12, 2		GROUP: 2811			
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EXAMINER INITIALS		DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)		
1	AA	5,019,882	05/28/1991		Solomon et al.	357	23.8	May I	5, 1989	
W	AB	5,534,713	07/09/1996	Ismail et al.		257	24	May 20, 1994		
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2	AJ	05 121450 A	15/05/1993		Japan	H01L	21/338	<u> </u>		
			OTHER ART (In	cluding Aut	hor, Title, Date, Pertir	nent Pages, etc.				
2	AM R. People and J.C. Bean, "Band Alignments Of Coherently Strained Ge _x Si _{1-x} / Si Heterostructures On <001> Ge _y Si _{1-y} Substrates"; Appl. Phys. Lett. 48 (8); pp. 538-539; February 24, 1986.									
X	AN G. Hock et al., "High Performance 0.25 μ m p-Type Ge/SiGe MODFETs"; Electronics Letters; Vol. 34; No. 19; pp. 1888-1889; September 17, 1998.									
W	AO	U. Konig and F. So IEEE Electron Dev	chaffler, "p-Type	Ge-Chann 14; No. 4;	el MODFET's With	n High Trans	conductanc	e Grown On	Si Substrates	
AMINER C	1)			DATE CONSIDERED MOSTOR					
AMDIED. 1-	deial :	if reference considered	whathar a			19	1000			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANCE INFORMATION					ATTY. DOCKET NO. YOR919990123US2	SERIAL NO.: 09/936,320					
DISCLOSURE STATEMENT				SCE OB	APPLICANT: Jack O. Chu						
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			OTHER ART (Inc	cluding Au	thor, Title, Date, Pertinent Pag	es, etc.)					
R	BE	M. Arafa, "A 70-4 Letters; Vol. 17; l			as Self-Aligned p-Type SiC ember 1996.	ie MODFE	T"; IEEE Ele	ctron De	vice		
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92		Milind Gokhale et al., "Enhanced Performace Of PMOS and CMOS Circuits Using Self-Aligned MOSFETs With Modulation Doped Si-Ge Channel"; Proceedings of the Tenth Biennial University/ Government/Industry Microelectronics Symposium; 1993 IEEE; US; New York; pp.219-222; May 18-19, 1993.									
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EXAMINER	J				DATE CONSIDERED	ul	05/107				
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